

Supplementary Materials: Improved Stability and Controllability in ZrN-Based Resistive Memory Device by Inserting TiO₂ Layer

Junhyeok Choi and Sungjun Kim

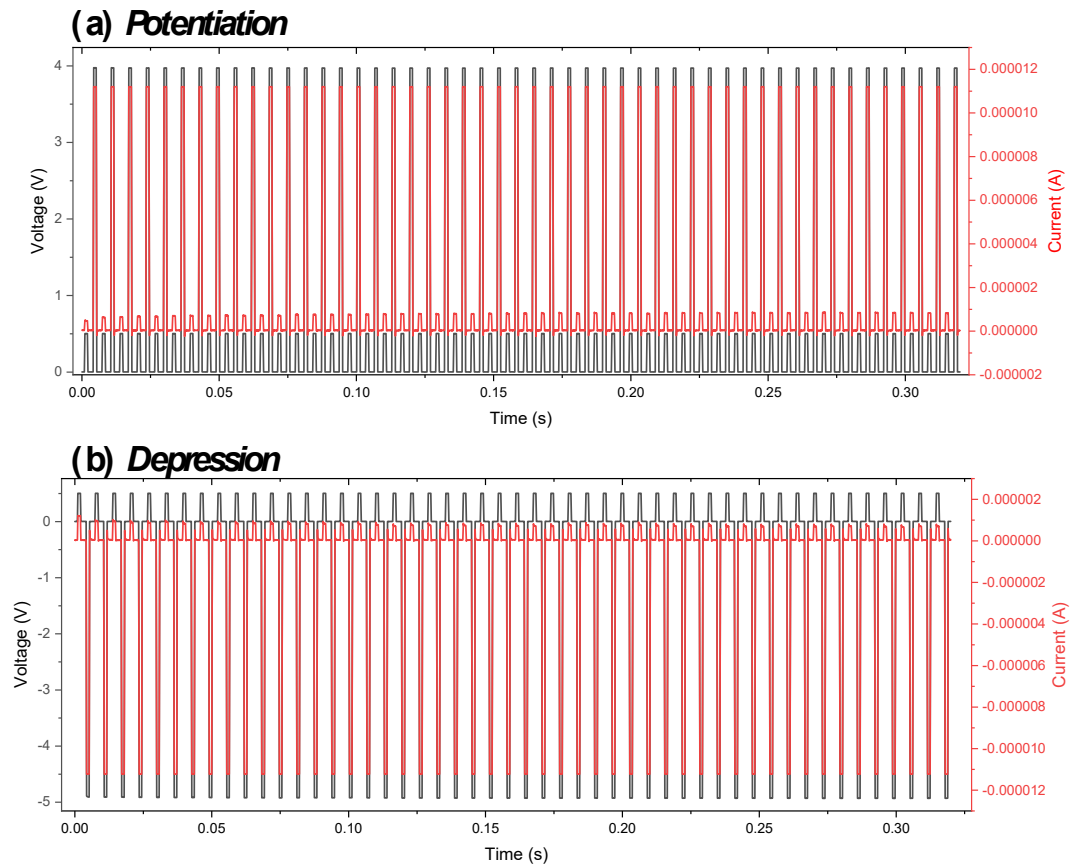


Figure S1. Transient characteristics for (a) potentiation and (b) depression of Ag/TiO₂/ZrN/Si device.